

Amendments to the Specification:

Please replace paragraph [0019] of the substitute specification filed on February 2, 2004 with the following amended paragraph:

[0019] Fig. 3 is a graph showing, in forming an AlN film, the relation between a ratio (V raw material gas/III raw material gas) and the FWHM in X-ray rocking curve. The abscissa axis designates the ratio (ammonia/trimethylaluminum~~trimethylaluminum~~), and the vertical axis designates the FWHM. If the FWHMs of AlN films are set to 90 arcsec or below, the resulting substrates having their respective AlN films are preferably usable as substrates for acoustic surface wave device. On the other hand, if the FWHMs of AlN films are set beyond 90 arcsec, the resulting substrates having their respective AlN films are not usable as substrates for acoustic surface wave devices. Therefore, as is apparent from Fig. 3, it is desired that the ratio of (ammonia/trimethylaluminum~~trimethylaluminum~~), that is, the ratio (V raw material gas/III raw material gas), is set to 800 or below.

Please replace paragraph [0021] of the substitute specification filed on February 2, 2004 with the following amended paragraph:

[0021] Moreover, the forming pressure of the AlN film is preferably set within a range of 7-17 Torr. That is, the interior pressure of the reactor is set to the above range. In this case, even though the ratio of (ammonia/trimethylaluminum~~trimethylaluminum~~) is largely fluctuated, the crystallinity of the AlN film can be easily developed to 90 arcsec or below in FWHM of X-ray rocking curve.